

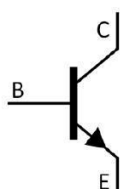
NPN 半导体三极管 Silicon NPN transistor
描述 / Descriptions

TO-126 塑封封装 NPN 半导体三极管。Silicon NPN transistor in a TO-126 Plastic Package.

特征 / Features 用途 / Applications

与 BD140 互补。用于中功率电路及开关电路。

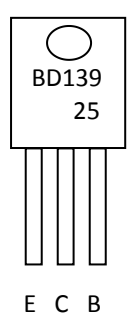
Complement to BD140. Medium power linear and switching applications

内部等效电路 / Equivalent Circuit
引脚排列 / Pinning


PIN1 : Emitter PIN 2 : Collector PIN 3 : Base

放大及印章代码 / hFE Classifications & Marking

*hFE(1)分档及打印

分 档	1	2				印记见下 具体内容以打印为准
H _{FE(1)}	100~200	160~320				
打印 (简例)	16	25				
其 它 说 明	封装外形: TO-126 管脚排列: E、C、B					

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V _{CB0}	80	V
Collector to Emitter Voltage	V _{CEO}	80	V
Emitter to Base Voltage	V _{EBO}	5.0	V
Collector Current - Continuous	I _C	1.5	A
Base Current – Continuous	I _B	0.5	A
Collector Power Dissipation	P _C	1.25	W
Collector Power Dissipation	P _C (T _c =25°C)	12.5	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Emitter Breakdown Voltage	V _{CEO}	I _C =30mA I _B =0	80			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =30V I _E =0			0.1	μA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =5.0V I _C =0			10	μA
DC Current Gain	h _{FE(1)}	V _{CE} =2.0V I _C =150mA	40		400	
	h _{FE(2)}	V _{CE} =2.0V I _C =500mA	25			
	h _{FE(3)}	V _{CE} =2.0V I _C =5.0mA	25			
Collector to Emitter Saturation Voltage	V _{CE(sat)}	I _C =500mA I _B =50mA			0.5	V
Base to Emitter On Voltage	V _{BE(on)}	V _{CE} =2.0V I _C =500mA			1.0	V

电参数曲线图 / Electrical Characteristic Curve
